



Air Force Invention No. AFB00670

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner of Patents and Trademarks, Washington, D.C. 20231-0001.

On 23 March 2004
(DATE OF DEPOSIT)

WILLIAM G. AUTON 31,320
NAME OF APPLICANT, ASSIGNEE, OR REG. REP.

 23 March 2004
SIGNATURE DATE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of
Richard A. Soref et al
Application Serial No. 10/722,611
Filed: 28 November 2003
For: **Strain-engineered Direct-Gap $\text{Ge}/\text{Sn}_x\text{Ge}_{1-x}$ Heterodiode and Multi-Quantum-Well Photodetectors, Lasers, Emitters and Modulators grown on $\text{Sn}_y\text{Si}_z\text{Ge}_{1-y-z}$ -buffered Silicon**

Honorable Commissioner of Patents and Trademarks
Washington D. C. 20231-0001

Sir:

RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS

In response to the Office Action of 27 February 2004, please consider the following amendment. A fee of \$130 is enclosed.

IN THE CLAIMS

Please retain all original claims.

04/07/2004 SZEWDIE1 00000007 010465 10772611

01 FC:1460 130.00 DA